



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>

NTE2336 Silicon NPN Transistor Darlington Switch ^w/Internal Damper & Zener Diode

Features:

- 60V Zener Diode Built-In Between Collector and Base
- Low Fluctuation in Breakdown Voltages
- High Energy Handling Capability
- High Speed Switching

Absolute Maximum Ratings: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

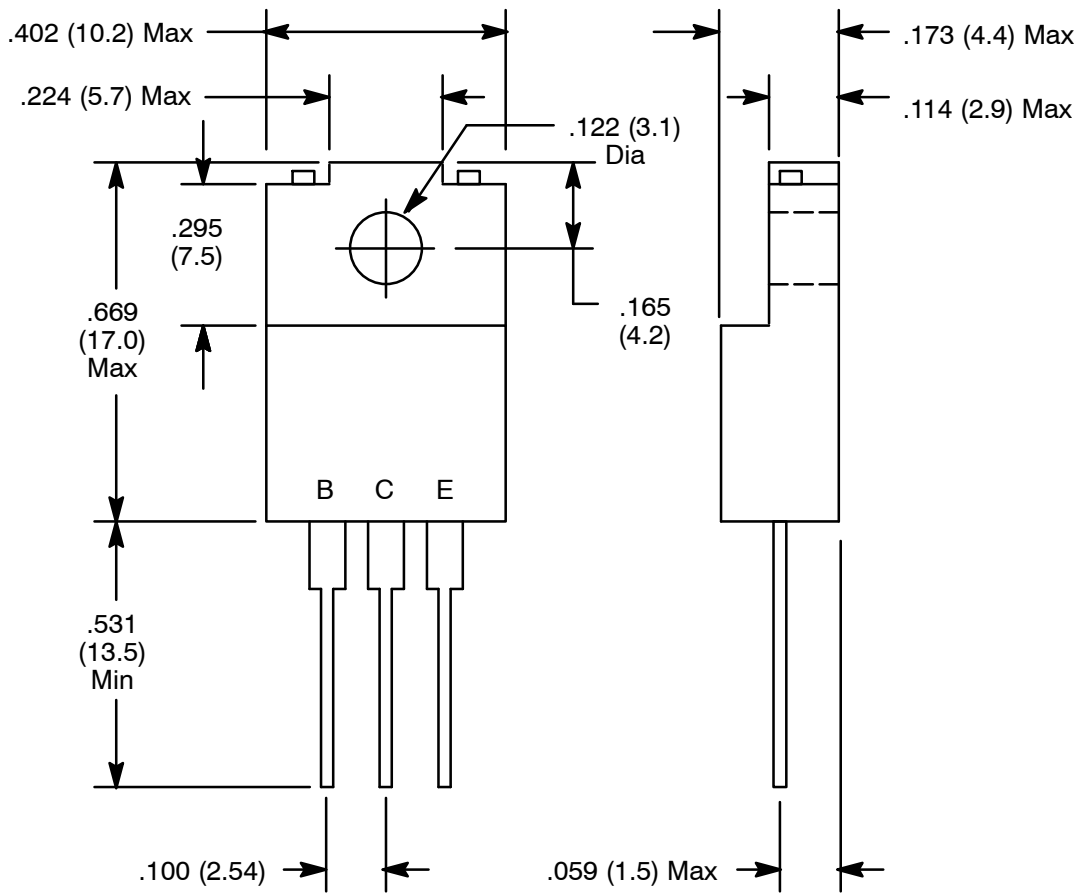
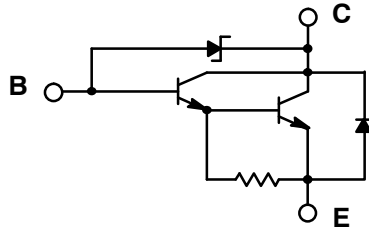
Collector-Base Voltage, V_{CBO}	60 \pm 10V
Collector-Emitter Voltage, V_{CEO}	60 \pm 10V
Emitter-Base Voltage, V_{EBO}	7V
Collector Current, I_C	
Continuous	8A
Peak	12A
Collector Power Dissipation ($T_C = +25^\circ\text{C}$), P_C	45W
Collector Power Dissipation ($T_A = +25^\circ\text{C}$), P_C	2W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 50V, I_E = 0$	-	-	100	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 7V, I_C = 0$	-	-	2	mA
Collector-Emitter Voltage	V_{CEO}	$I_C = 5mA, I_B = 0$	50	-	70	V
DC Current Gain	h_{FE}	$V_{CE} = 3V, I_C = 4A$	2000	-	5000	
		$V_{CE} = 3V, I_C = 8A$	500	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 4A, I_B = 8mA$	-	-	1.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 4A, I_B = 8mA$	-	-	2.0	V
Transition Frequency	f_T	$V_{CE} = 10V, I_C = 500mA, f = 1MHz$	-	20	-	MHz

Electrical Characteristics (Cont'd): ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Time	t_{on}	$V_{CC} = 50\text{V}, I_C = 4\text{A},$ $I_{B1} = 8\text{mA}, I_{B2} = -8\text{mA}$	-	0.5	-	μs
Storage Time	t_{stg}		-	4	-	μs
Fall Time	t_f		-	1	-	μs
Energy Handling Capacity	$E_{s/b}$	$I_C = 1\text{A}, L = 100\text{mH}, R_{BE} = 100\Omega$	50	-	-	mJ



NOTE: Tab is isolated